

Page 8, delete lines 21-29.

Page 9, delete lines 1-16; and

line 17, change "[Best Mode for Carrying Out the Invention]" to

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS--

Page 32, line 21, change "22" to --1422--; and

line 27, change "21" to --1421--.

Page 34, line 1, change "20" to --18--.

IN THE CLAIMS:

Please amend claims 1-16 as follows:

1. (Amended) A thin film transistor including [on the surface side of a substrate]
a plurality of component parts comprising:
 - a channel region; [opposed to]
 - a gate electrode opposed to the channel region;[, with]
 - a gate insulating film provided [therebetween, and] between the channel region
and the gate electrode;
 - a source-drain region connected to said channel region[, and a thin film
transistor having];
 - a source-drain wiring layer electrically connected to said source-drain
region[,]; and
 - a gate wiring layer electrically connected to said gate electrode,

[in which] at least one of the component [part composed of] parts being
formed from a conductive film or a semiconductor film[, among the component parts of each
thin film transistor , is] and being provided with a radiating extension extending outwardly
from the at least one component part.

Fig. 1 B 2. (Amended) [Thin] The thin film [transistors] transistor according to Claim 1, wherein said ~~radiating~~ ^{heat dissipating} extension [is a portion extending] extends outwardly from both sides of said gate electrode [at both sides].

Fig. 1 B 3. (Amended) [Thin] The thin film [transistors] transistor according to Claim 2, wherein the [extending portion] ~~radiating~~ ^{heat dissipating} extension of said gate electrode is provided on at least one end of said gate electrode.

Fig. 5 4. (Amended) [Thin] The thin film [transistors] transistor according to Claim 3, wherein said gate wiring layer is electrically connected to the [extending portion] ~~radiating~~ ^{heat dissipating} extension of said gate electrode by a plurality of contact holes.

Fig. 2 B 5. (Amended) [Thin] The thin film [transistors] transistor according to Claim 2, wherein the [extending portion] ~~radiating~~ ^{heat dissipating} extension of said gate electrode is provided in a [region where the extending portion of said gate electrode is] position opposed to said channel region.

Fig. 2 B 6. [Thin] The thin film [transistors] transistor according to Claim 5, wherein the [extending portion] ~~radiating~~ ^{heat dissipating} extension of said gate electrode is provided at a location corresponding to an approximately central region of [the width of] said channel region.

Fig. 3 B 7. (Amended) [Thin] The thin film [transistors] transistors according to Claim 1, wherein said ~~radiating~~ ^{heat dissipating} extension [is a portion extending] extends from both sides of said channel region [to both sides].

Fig. 3 B 8. (Amended) [Thin] The thin film [transistors] transistor according to Claim 7, wherein the [extending portion] ~~radiating~~ ^{heat dissipating} extension of said channel region is provided in a [region] position opposed to said gate electrode.

Fig. 4 B 9. (Amended) [Thin] The thin film [transistors] transistor according to Claim 7, wherein said radiating extension [is a portion extending] extends from both sides of said source-drain region [to at both sides].

Fig. 5 10. (Amended) [Thin] The thin film [transistors] transistor according to Claim 9,

wherein said source-drain wiring layer is electrically connected to the [extending portion]

B heat dissipating
A radiating extension of said source-drain region by a plurality of contact holes.

Fig. 6 11. (Amended) [Thin] A CMOS inverter circuit comprising two of the thin film

transistors according to Claim 1, wherein said heat dissipating
A radiating extension [is an extending portion

extended] extends from both sides of said source-drain region [at both sides so that, in a

CMOS inverter circuit including], said thin film transistors[, which are] having an [inversely

conductive] inverse conductivity type from each other, [the] adjacent source-drain regions of

said thin film transistors [are] being connected [between CMOS circuits].

12. (Amended) [Thin film transistors] The CMOS inverter circuit according to

Claim 11, wherein said heat dissipating
A radiating extension is provided with a conductivity by using an

B impurity identical to [the] an impurity of said source-drain region to which said heat dissipating
A radiating extension [itself] is connected.

13. (Amended) [Thin film transistors] The CMOS inverter circuit according to

B heat dissipating
A Claim 11 [or 12], wherein said radiating extension is formed in a region opposed to said source-drain wiring layer [for], said source-drain wiring layer connecting the adjacent source-drain regions of said thin film transistors [between the CMOS circuits].

Fig. 7 14. (Amended) [Thin] The thin film [transistors] transistor according to claim 1,

B heat dissipating
A wherein said radiating extension [is an extending portion] extends from both sides of at least [either] one of said source-drain wiring layer and said gate wiring layer [at both sides].

15. (Amended) A liquid crystal display device [using] comprising an active matrix substrate on which a driving circuit including a thin film transistor as defined in [any of Claims] Claim 1 [to 14] is formed.

16. (Amended) An electronic apparatus [in which] comprising a liquid crystal display device as defined in Claim 15 [is used].

Please add new claims 17-21 as follows:

--17. The thin film transistor according to Claim 1, said plurality of component parts each extending in a longitudinal direction, the ~~radiating~~ ^{heat dissipating} extension extending in a direction substantially perpendicular to the longitudinal direction.--

--18. A liquid crystal display device comprising an active matrix substrate on which a driving circuit including a CMOS inverter circuit as defined in Claim 11 is formed.--

--19. An electronic apparatus comprising a CMOS inverter circuit as defined in Claim 11.--

--20. The liquid crystal display device according to Claim 18, said plurality of component parts each extending in a longitudinal direction, the ~~radiating~~ ^{heat dissipating} extension extending in a direction substantially perpendicular to the longitudinal direction.--

--21. The electronic apparatus according to Claim 19, said plurality of component parts each extending in a longitudinal direction, the ~~radiating~~ ^{heat dissipating} extension extending in a direction substantially perpendicular to the longitudinal direction.--